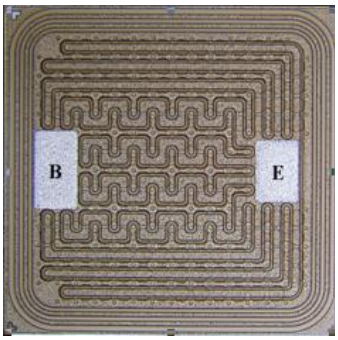
M3DD1260D

General Description

This chip can be turned into various silion NPN triple diffused plannar transistor by using different package format, mainly used in power switch circuit of charger and adapter.

Die Data

Die Drawing			
	Die Size (mm×mm)		2.60×2.60
	Die Thickness (μm)		260
	Bonding Pad Size (μm^2)	Base	620×350
		Emitter	500×350
	Front Metal / Thickness		AL/5.5μm
	Back Metal		Ag
	Wafer Diameter (mm)		Φ150
	Die Attach Method		Solder

Absolute Maximum Ratings (Ta= 25℃ unless otherwise noted)

Parameter		Symbol	Value	Unit	Recommend Package
Collector-Base Voltage		V_{CBO}	700	V	TO-220AB
Collector-Emitter Voltage		V_{CEO}	400	V	
Emitter- Base Voltage		V_{EBO}	9	V	
Collector Current（DC）		I_C	4.0	A	
Collector Peak Current（tp＜5ms）		I_{CM}	8.0	A	
Base Current（DC）		I_B	2.0	A	
Base Peak Current（tp＜5ms）		I_{BM}	4.0	A	
Total Power Dissipation	Ta=25℃	P_{tot}	2	W	
	Tc=25℃		75		
Junction Temperature		T_j	150	℃	
Storage Temperature Range		T_{stg}	-55～150	℃	

Electrical Characteristics (Ta= 25℃ unless otherwise noted)

Parameter	Symbol	Test Conditions	Criterion			Unit
			Min.	Typ.	Max.	
Collector-Base Cut-off Current	I_{CBO}	V_{CB}=700V, I_E=0			0.1	mA
Collector-Emitter Cut-off Current	I_{CEO}	V_{CE}=400V, I_B=0			0.1	mA
Emitter-Base Cut-off Current	I_{EBO}	V_{EB}=9V, I_C=0			0.1	mA
Collector-Base Voltage	V_{CBO}	I_C=0.1mA	700			V
Collector-Emitter Voltage	V_{CEO}	I_C=1mA	400			V

Emitter- Base Voltage	V_{EBO}	I_E=0.1mA	9			V
DC Current Gain	h_{FE}*	V_{CE}=5V, I_C=1.0A	15		35	
Ratio Between h_{FE1} and h_{FE2}	h_{FE1}/ h_{FE2}	h_{FE1}:V_{CE}=5V, I_C=5mA h_{FE2}:V_{CE}=5V, I_C=1A	0.75	0.9		
Collector-Emitter Saturation Voltage	$V_{CE\ sat}$*	I_C=2.0A, I_B=0.5A		0.30	1.0	V
Base- Emitter Saturation Voltage	$V_{BE\ sat}$*	I_C=2.0A, I_B=0.5A		0.90	1.5	V
Storage Time	t_s	UI9600，I_C=0.5A	2.0		6.0	μs
Rise Time	t_r				1	μs
Fall Time	t_f				0.6	μs
Transition Frequency	f_T	V_{CE}=10V, I_C=0.5A f=1MHz	5			MHz
* Impulse Test Pulse Width tp≤300μs ; Duty Cycle δ≤2%						

About of Hazardous Substance

Part's Name	Hazardous Substance									
	Pb	Hg	Cd	Cr(VI)	PBB	PBDE	DIBP	DEHP	DBP	BBP
（Limit）	≤0.1%	≤0.1%	≤0.01%	≤0.1%	≤0.1%	≤0.1%	≤0.1%	≤0.1%	≤0.1%	≤0.1%
Chip	○	○	○	○	○	○	○	○	○	○
Front Side	○	○	○	○	○	○	○	○	○	○
Back Side	○	○	○	○	○	○	○	○	○	○
Notes	○：Means the hazardous material is under the criterion of 2011/65/EU. ×：Means the hazardous material exceeds the criterion of 2011/65/EU .									

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